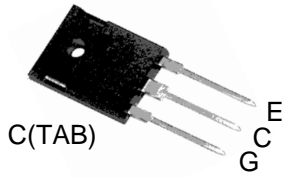
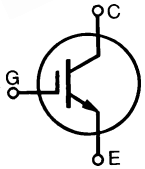


# SG20N12T, SG20N12DT

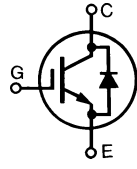
## Discrete IGBTs



G=Gate, C=Collector,  
E=Emitter, TAB=Collector

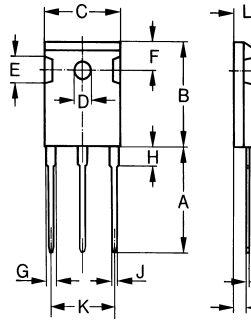


SG20N12T



SG20N12DT

Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Symbol	Test Conditions	Maximum Ratings	Unit
<b>V<sub>CES</sub></b> <b>V<sub>CGR</sub></b>	T <sub>J</sub> =25°C to 150°C T <sub>J</sub> =25°C to 150°C; R <sub>GE</sub> =1 MΩ;	1200 1200	V
<b>V<sub>GES</sub></b> <b>V<sub>GEM</sub></b>	Continuous Transient	±20 ±30	V
<b>I<sub>C25</sub></b> <b>I<sub>C90</sub></b> <b>I<sub>CM</sub></b>	T <sub>C</sub> =25°C T <sub>C</sub> =90°C T <sub>C</sub> =25°C, 1 ms	40 20 80	A
<b>SSOA</b> <b>(RBSOA)</b>	V <sub>GE</sub> =15V; T <sub>VJ</sub> =125°C; R <sub>G</sub> =47Ω Clamped inductive load	I <sub>CM</sub> =40 @ 0.8 V <sub>CES</sub>	A
<b>P<sub>c</sub></b>	T <sub>C</sub> =25°C	150	W
<b>T<sub>J</sub></b> <b>T<sub>JM</sub></b> <b>T<sub>stg</sub></b>		-55...+150 150 -55...+150	°C
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10s Maximum Tab temperature for soldering SMD devices for 10s	300 260	°C
<b>M<sub>d</sub></b>	Mounting torque (M3)	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g

(T<sub>J</sub>=25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			Unit
		min.	typ.	max.	
<b>BV<sub>CES</sub></b>	I <sub>C</sub> =1 mA; V <sub>GE</sub> =0V	1200			V
<b>V<sub>GE(th)</sub></b>	I <sub>C</sub> =250 μA; V <sub>CE</sub> =V <sub>GE</sub>	2.5		5.0	V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> =V <sub>CES</sub> ; T <sub>J</sub> =25°C V <sub>GE</sub> =0V; T <sub>J</sub> =125°C			250 1	μA mA
<b>I<sub>GES</sub></b>	V <sub>CE</sub> =0V; V <sub>GE</sub> =±20V			±100	nA
<b>V<sub>CE(sat)</sub></b>	I <sub>C</sub> =I <sub>C90</sub> ; V <sub>GE</sub> =15V		2.0	2.5	V

**Sirectifier**®

# SG20N12T, SG20N12DT

## Discrete IGBTs

(T<sub>J</sub>=25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			Unit
		min.	typ.	max.	
g <sub>ts</sub>	I <sub>C</sub> =I <sub>C90</sub> ; V <sub>CE</sub> =10V Pulse test, t <sub>test</sub> ≤300us, duty cycle≤2%	12	16		S
C <sub>ies</sub> C <sub>oes</sub> C <sub>res</sub>	V <sub>CE</sub> =25V; V <sub>GE</sub> =0V; f=1MHz		1750 90 31		pF
Q <sub>g</sub> Q <sub>ge</sub> Q <sub>gc</sub>	I <sub>C</sub> =I <sub>C90</sub> ; V <sub>GE</sub> =15V; V <sub>CE</sub> =0.5V <sub>CES</sub>		63 13 26		nC
t <sub>d(on)</sub> t <sub>ri</sub> t <sub>d(off)</sub> t <sub>fi</sub> E <sub>off</sub>	Inductive load, T <sub>J</sub> =25°C I <sub>C</sub> =I <sub>C90</sub> ; V <sub>GE</sub> =15V; L=100uH; V <sub>CE</sub> =0.8V <sub>CES</sub> ; R <sub>G</sub> =R <sub>off</sub> =47 Ω Remarks: Switching times may increase for V <sub>CE</sub> (Clamp) > 0.8V <sub>CES</sub> ; higher T <sub>J</sub> or increased R <sub>G</sub>		28 20 400 380 6.5	800 700 10.5	ns ns ns ns mJ
t <sub>d(on)</sub> t <sub>ri</sub> E <sub>on</sub> t <sub>d(off)</sub> t <sub>fi</sub> E <sub>off</sub>	Inductive load, T <sub>J</sub> =125°C I <sub>C</sub> =I <sub>C90</sub> ; V <sub>GE</sub> =15V; L=100uH; V <sub>CE</sub> =0.8V <sub>CES</sub> ; R <sub>G</sub> =R <sub>off</sub> =47 Ω Remarks: Switching times may increase for V <sub>CE</sub> (Clamp) > 0.8V <sub>CES</sub> ; higher T <sub>J</sub> or increased R <sub>G</sub>		30 27 0.90 700 550 9.5		ns ns mJ ns ns mJ
R <sub>thJC</sub>				0.83	K/W
R <sub>thCK</sub>			0.25		K/W

### Reverse Diode (FRED)

(T<sub>J</sub>=25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			Unit
		min.	typ.	max.	
V <sub>F</sub>	I <sub>F</sub> =12A; T <sub>VJ</sub> =150°C T <sub>VJ</sub> =25°C			1.87 2.15	V
I <sub>RM</sub>	V <sub>R</sub> =540V; I <sub>F</sub> =20A; -di <sub>F</sub> /dt=100A/us L≤0.05uH; T <sub>VJ</sub> =100°C		7		A
t <sub>rr</sub>	I <sub>F</sub> =1A; -di <sub>F</sub> /dt=100A/us; V <sub>R</sub> =30V; T <sub>VJ</sub> =25°C		40	60	ns
R <sub>thJC</sub>				1.6	K/W

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